

Please replace the paragraph beginning at page 8, line 9, with the following rewritten paragraph:

B² --The diffusion blocking characteristics of the first dopant blocking layer 104 can be seen most readily from a review of Fig. 2. To this end, the concentration of the illustrative dopant, Zn, shown at 201, is relatively high in the layer of p-type InP (on the order of about $2 \times 10^{18}/\text{cm}^3$). However, the concentration of Zn drops off significantly in the illustrative dopant blocking layer InAlAs layer 202, grown at low temperature as discussed above. The illustrative layer of InAlAs shown in Fig. 2 is about 800Å thick, and as can be seen, the concentration of Zn drops off to minimal levels.--

IN THE CLAIMS

Amend claim 14 as follows:

- 1 14. (Amended) A process as recited in claim 1, wherein said first and said
2 second dopant blocking layers are formed by MOVPE.

B³ [Amend claim 15 as follows:]

- 1 15. (Amended) A process as recited in claim 1, wherein said first and said
2 second dopant blocking layers are formed by MBE.

Add the following claims:

- 1 59. A process as recited in claim 1 wherein the first and second dopant
2 blocking layers are disposed between a semi-insulating layer and a p-type layer.

- B⁴ 1 60. A process as recited in claim 59 wherein the p-type layer includes a Zn
2 dopant, and the semi-insulating layer includes an Fe dopant.

- 1 61. A process as recited in claim 20 wherein the first and second dopant
2 blocking layers are disposed between a semi-insulating layer and a p-type layer.

- 1 62. A process as recited in claim 61 wherein the p-type layer includes a Zn
2 dopant, and the semi-insulating layer includes an Fe dopant.